

SEMICONDUCTOR DICET-03-05
T-01-05**SWITCHING DIODES****ZETEX SEMICONDUCTORS**

Dice type	Description	$V_{(BR)}$ Min.	V_F Max. at I_F		I_R Max. at V_R		T_{rr} Typical	Geometry
		Volts	Volts	mA	μA	Volts	nS	
BAS21	High voltage single diode	250	1.0	100	0.1	200	50*	G24
HD3A	Single diode	85	1.0	10	1.0	75	6	G25
HD2A	Dual (common cathode)	85	1.0	10	1.0	75	6	G26
FD2A	Dual (common cathode)	60	1.2	100	1.0	60	2	G27
FD2RA	Dual (common anode)	60	1.2	100	1.0	60	5	G28

* Maximum value

Switching conditions: BAS21 $I_F = 30mA$, to $I_R = 30mA$, $R_L = 100\Omega$ measured @ $I_R = 3mA$.HD3A/HD2A $I_F = 10mA$, $I_R = 10mA$, $I_{rr} = 1mA$.FD2A/FD2A $I_F = 10mA$, $V_R = 6V$, $R_L = 100\Omega$, Recover to 10% I_R , Peak.**LOW LEAKAGE DIODES**

Dice type	Description	$V_{(BR)}$ Min.	V_F Max. at I_F		I_R Typical at V_R		Geometry
		Volts	Volts	mA	nA	Volts	
LD2A	Dual (common cathode)	100	1.4	200	1.0	100	G29
LD2RA	Dual (common anode)	100	1.4	200	5.0	100	G29